

Search History

L Number	Hits	Search Text	DB	Time stamp
1	19	(coating coated) near6 Q-switch and passive adj2 Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:12
2	0	(coating coated) near6 Q-switch and passive adj2 Q-switch near6 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:12
3	2	(coating coated) near6 Q-switch and passive adj2 Q-switch and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:20
4	2	(coating coated) near12 Q-switch and passive adj2 Q-switch and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:24
5	0	(coating coated) near12 saturable adj absorber and passive adj2 Q-switch and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:10
6	6	(optical optically) near6 (polish polishing polished) and passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:13
8	0	(polish polishing polished) near12 passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:14
9	32	(polish polishing polished) and passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:14
10	4	(polish polishing polished) and passive adj Q-switch.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:20
11	3989	(polish polishing polished) near6 lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:20
12	1	(polish polishing polished) near6 lens and laser and Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
13	1870	(polish polishing polished) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
14	542	(polish polishing polished) near6 lens.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23
15	0	(polish polishing polished) near6 lens near6 reflection.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:23

16	11	(polish polishing polished) near6 lens near6 reduce.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 11:47
17	1876	(polish polishing polished) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 11:47
18	533	(optical optically) near12 (polish polishing polished) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 11:47
19	471	(optical optically) near12 (polish polishing polished) near6 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 11:49
20	361	(optical optically) near6 (polish polishing polished) near6 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 11:49
21	188	(optical optically) near3 (polish polishing polished) near3 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 11:51
22	74	(optical optically) near1 (polish polishing polished) near3 lens.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 12:31
23	8	(optical optically) near1 (polish polishing polished) and Q-switch.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 12:44
24	59	output adj (coupler coupling) near8 Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 13:04
25	22	(mqw multiple adj quantum adj well) and q-switch and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 13:07
26	3	(mqw multiple adj quantum adj well).ti,ab,clm. and q-switch and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 13:09
27	1570	(mqw multiple adj quantum adj well).ti,ab,clm. and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 13:09
28	227	(mqw multiple adj quantum adj well).ti. and laser.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 13:09
29	192	(mqw multiple adj quantum adj well).ti. and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/29 13:11

30	12	{mqw multiple adj quantum adj well) near6 advantage and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:36
31	2	("5832008").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:53
32	0	("passivcadjQ-switchnear12(inpindiumadjphosphideidegaasalalgaasgaalasgalliumadjaluminumadjarsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:55
33	0	passive adj Q-switch near15 (inp indium phosphide ide gaasal algaas gaalas gallium adj alumin?um adj arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 13:55
34	0	passive adj Q-switch near15 (inp indium phosphide ide gaasal algaas gaalas gallium adj alumin\$um adj arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 14:16
35	14493	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/75) or (372/10) or (372/11) or (372/12) or (372/13) or (372/14) or (372/15) or (372/16)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 14:18
36	7	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/75) or (372/10) or (372/11) or (372/12) or (372/13) or (372/14) or (372/15) or (372/16)).CCLS.) and (algaas inp gallium adj alumin\$lum adj arsenide alumin\$lum adj gallium adj arsenide indium adj phosphide) and passive adj (Q-switch Q-switching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 14:20
-	243	q-switch.ti. and laser.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 19:49
-	215	q-switch.ti. and laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 10:17
-	2	q-switch.ti. and laser.ti. and (fabry-perot or f-p).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:05
-	31	passive adj (q-switch or q-switching) and semiconductor and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:15
-	6	passive adj (q-switch or q-switching).ti,ab. and semiconductor and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:16
-	3	passive adj (q-switch or q-switching).ti,ab. and semiconductor.ti,ab. and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 11:16

-	17	(US-6351478-\$ or US-6340806-\$ or US-6335942-\$ or US-3660777-\$ or US-6400495-\$ or US-5274650-\$ or US-5408480-\$ or US-5461637-\$ or US-5005176-\$ or US-5541948-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6172997-\$ or US-6259711-\$ or US-6263004-\$ or US-6240113-\$ or US-6061378-\$).did.	USPAT; EPO; DERWENT	2002/07/13 11:17
-	0	(US-6351478-\$ or US-6340806-\$ or US-6335942-\$ or US-3660777-\$ or US-6400495-\$ or US-5274650-\$ or US-5408480-\$ or US-5461637-\$ or US-5005176-\$ or US-5541948-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6172997-\$ or US-6259711-\$ or US-6263004-\$ or US-6240113-\$ or US-6061378-\$).did.	USPAT; EPO; DERWENT	2002/07/13 11:18
-	284	(372/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:18
-	157	(372/11).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:18
-	5180	(372/43).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:29
-	4	((372/11).CCLS.) and ((372/43).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:43
-	178	(passive or passively) near3 (q-switch or q-switching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:19
-	0	((372/11).CCLS.) and ((372/43).CCLS.)) and ((passive or passively) near3 (q-switch or q-switching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:19
-	95	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3) and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 13:44
-	22	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:36
-	5	semiconductor.ti,ab. and laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls. and passive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:45
-	11	laser.ti,ab. and (q-switch or q-switching or passive\$2 near3 switch\$3).ti,ab. and 372/\$6.ccls. and (variable or vary) near4 wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 15:48

-	1	semiconductor adj laser and (passively or passive) adj (q-switch or q-switching) and (variable or vary or varies) near3 (wavelength or frequency or frequencies)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:02
-	157	(372/11).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:02
-	43	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:03
-	0	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and q-switch near4 (tune or variable) near4 (wavelength or frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	0	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and q-switch near12 (tune or variable) near12 (wavelength or frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	15	((372/11).CCLS.) and semiconductor near3 (laser or q-switch)) and ((tune or tuning) near12 (wavelength or frequency))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 16:04
-	5578	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:30
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (coated or coating) near12 (reflector or reflecting or reflect) near12 thickness near12 (infrared or infra-red or IR) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:33
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:34
-	0	((372/10).CCLS.) or ((372/11).CCLS.) or ((372/43).CCLS.) and (layer or film or cover or covering or coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:35
-	0	(layer or film or cover or covering or coated or coating or coat) near12 (reflector or reflecting or reflect) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:35
-	27	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 17:36
-	14	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively) and semiconductor near12 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:13

-	18	(layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and Q-switch\$3 near12 (passive or passively) and semiconductor near12 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:13
-	4	((layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and Q-switch\$3 near12 (passive or passively) and semiconductor near12 laser) not ((layer or film or cover or covering or coated or coating or coat) near12 (thick or thickness) and (Q-switch or Q-switching) near12 (passive or passively) and semiconductor near12 laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:27
-	1	ar adj coating near12 (gradient or variable or graded or non-uniform or nonuniform) and q-switch\$3 near12 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:33
-	1	coating near12 (gradient or variable or graded or non-uniform or nonuniform) and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:35
-	1	graded near12 coating and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:36
-	1	graded near12 coat\$3 and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:36
-	5	ar near12 coat\$3 and passive\$2 near12 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 18:53
-	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 19:11
-	0	("modulat\$3 near12 (thickness or coat\$3) near12 q-switch\$3").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 19:11
-	3	modulat\$3 near12 (thickness or coat\$3) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 19:15
-	1	modulat\$3 near12 (ar or anti-reflective or antireflective) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/13 19:15
-	6749	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCIS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 11:04
-	19	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and passive\$2 near10 q-switch\$3 and semiconductor and coat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:39

-	0	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded adj2 ar adj coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:40
-	0	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded near4 ar adj coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:40
-	0	((372/10) or (372/11) or (372/14) or (372/15) or (372/16) or (372/43) or (372/75)).CCLS.) and graded near4 coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:41
-	1	graded near4 (antireflective or ar) adj2 coatings near4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:42
-	1	graded near4 (antireflective or ar) adj2 coatings near4 (thick or thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:43
-	6585	graded adj index (antireflective or ar) adj2 coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 13:43
-	1	graded adj index adj (antireflective or ar) adj coating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 14:31
-	6	graded near9 (antireflective or ar) adj coating same thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:10
-	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:14
-	0	("66160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:15
-	2	("6160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:16
-	1	((tune or tuning) near12 q-switch\$3) near12 (translat\$3 or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:46
-	0	rotation-induced near12 (tune or tuning) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:47
-	0	translation-induced near12 (tune or tuning) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:47

-	0	translation-induced near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:47
-	0	rotation-induced near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:47
-	87	rotat\$3 near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:48
-	43	(rotate or rotation) near12 (tune or tuning) and q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:48
-	7	(rotate or rotation) near12 (tune or tuning) and q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 16:25
-	0	(rotate or rotation) near12 (tune or tuning) and passive\$2 near3 q-switch\$3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 15:49
-	4	713436.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 16:30
-	4	semiconductor near2 passive\$2 near3 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 17:15
-	7	(infrared or ir) adj absorption near6 gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 17:43
-	4	(mqw or (multiple-quantum-well or multiple adj quantum adj well)) near3 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 18:24
-	0	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3 near12 passive\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 18:26
-	5	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 20:42
-	0	(inp or algaas or indium adj phosphide or aluminum adj gallium adj arsenide) near12 q-switch\$3 and passive\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 18:26
-	3	("5015353").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/14 20:43

-	3	("4868834").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/14 20:43
-	2	("6215805").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:33
-	12594	((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:36
-	412	372/12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:36
-	244	372/13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:36
-	244	372/13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	110	372/14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	143	372/15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	112	372/16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	13339	((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:37
-	60	((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16) and (passive or passively) near3 (Q adj switch or Q-switch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:38
-	28	((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16) and (passive or passively) near3 (Q adj switch or Q-switch)) and (rotat\$3 or translat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 17:57
-	7	((((372/10) or (372/11) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) or 372/12 or 372/13 or 372/13 or 372/14 or 372/15 or 372/16) and (passive or passively) near3 (Q adj switch or Q-switch)) and (rotat\$3 or translat\$3) near12 axis	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/18 18:42

-	4	618431.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 18:52
-	0	rotat\$3 near12 (Q-switch or Q adj switch) near12 tun\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 18:53
-	3	rotat\$3 near12 (Q-switch or Q adj switch) and tun\$3 and 372/4\$1.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 18:57
-	10	(rotate or rotating) near12 (Q-switch or Q adj switch) and (tune or tuning) and (372/4\$1.ccls. or 372/1\$1.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 19:22
-	1186	(372/75).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 19:22
-	8	((372/75).CCLS.) and (Q-switch or Q adj switch) near6 (passive or passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 19:24
-	0	((372/75).CCLS.) and (Q-switch or Q adj switch) near6 (passive or passively) same (moving or move or translate or translation or rotate or rotation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/18 19:24
-	4	618431.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/12 08:42
-	33	(US-6340806-\$ or US-6400495-\$ or US-6351478-\$ or US-5005176-\$ or US-5274650-\$ or US-5832008-\$ or US-5408480-\$ or US-6292504-\$ or US-6252892-\$ or US-6026101-\$ or US-6373864-\$ or US-6373865-\$ or US-3660777-\$ or US-5023878-\$ or US-5257274-\$ or US-6335942-\$ or US-6330259-\$ or US-5541948-\$ or US-5414724-\$ or US-5461637-\$ or US-6215805-\$ or US-6160824-\$ or US-5015353-\$ or US-4868834-\$).did. or (US-20020141457-\$ or US-20030007520-\$ or US-20030031215-\$ or US-20020051470-\$).did. or (US-3660777-\$ or US-5541948-\$).did. or (US-6240113-\$ or US-6172997-\$ or US-6061378-\$ or US-6263004-\$ or US-6259711-\$).did.	USPAT; US-PGPUB; EPO; DERWENT	2003/09/28 10:27
-	0	tunable near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 (varying variable adjusting adjustment selection selecting setting) near12 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:30
-	0	tunable near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:31

-	0	(tuning tune tunable) near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:31
-	0	(tuning tune tunable) near3 (Q adj switch Q-switch Q-switching Q adj switching) near12 (thickness optical adj path)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:32
-	1595	(Q-switch Q adj switch).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:32
-	315	(Q-switch Q adj switch).ti,ab,clm. and (thickness optical adj path path adj length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:32
-	62	(Q-switch Q adj switch).ti,ab,clm. and (thickness optical adj path path adj length) and (tune tuning tunable)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 10:43
-	33	(Q-switch Q-switching Q adj switch Q adj switching) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:29
-	2	semiconductor.ti,ab,clm. and (Q-switch Q-switching Q adj switch Q adj switching) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:30
-	3	(257/\$9.ccls. 372/4\$1.ccls. 372/50.ccls. semiconductor.ti,ab,clm.) and (Q-switch Q-switching Q adj switch Q adj switching) near6 lens.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:56
-	156	(Q-switch Q-switching Q adj switching Q adj switch).ti,ab,clm. and saturable adj absorb\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:57
-	46	(passive near2 (Q-switch Q-switching Q adj switching Q adj switch).ti,ab,clm. and saturable adj absorb\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 11:59
-	5	(passive near2 (Q-switch Q-switching Q adj switching Q adj switch).ti,ab,clm. and saturable adj absorb\$3 and (graded gradient variable near3 thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 12:00
-	5	(passive near2 (Q-switch Q-switching Q adj switching Q adj switch).ti,ab,clm. and saturable adj absorb\$3 and (graded gradient variable near3 thickness) and passive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 12:40
-	3	("4519082" "4644550" "4672619").PN.	USPAT	2003/09/28 12:24
-	2	4833333.URPN.	USPAT	2003/09/28 12:24
-	2	("6180824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 12:41
-	2	("6160824").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/28 13:02

2	("4833333").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 13:05
2	("5802083").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 13:05
0	("semiconductorand((Qadj(switchswitching))Q-switch Q-switching) near3 (passive passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 19:53
61	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 19:53
21	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:15
47	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient transmittance coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:20
26	(semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient transmittance coating coated)) not (semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:16
43	semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary graded grading gradient) near2 thickness transmittance coating coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 20:21
26	(semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary graded grading gradient) near2 thickness transmittance coating coated)) not (semiconductor and ((Q adj (switch switching)) Q-switch Q-switching) near3 (passive passively) and ((variable varying varies vary) near2 thickness graded grading grade gradient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:07
21	(lithium adj fluoride lif) near6 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:11
2	laser and host adj material near6 ("ho.sup.3+" holmium) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:10
13	(lithium adj fluoride lif) near3 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:24

-	2	y1f adj laser.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:26
-	0	semiconductor adj passive adj Q-switch and lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:26
-	0	semiconductor adj passive adj Q-switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/28 21:26